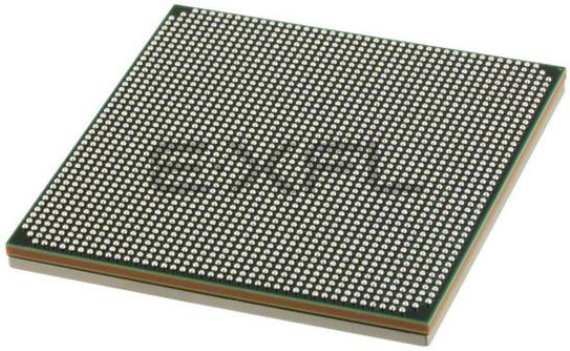

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	54150
Number of Logic Elements/Cells	693120
Total RAM Bits	54190080
Number of I/O	720
Number of Gates	-
Voltage - Supply	0.97V ~ 1.03V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1924-BBGA, FCBGA
Supplier Device Package	1926-FCBGA (45x45)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7vx690t-2ff1926i

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} have the same recommended voltage levels then they can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTX/GTH transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} - V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} - V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 7 shows the minimum current, in addition to I_{CCQ}, that is required by Virtex-7 T and XT devices for proper power-on and configuration. If the current minimums shown in Table 6 and Table 7 are met, the device powers on after all five supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the XPower tools to estimate current drain on these supplies.

Table 7: **Power-On Current for Virtex-7 T and XT Devices**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	I_{CCAUX_IO}	I_{CCBRAM}	Units
	Typ(1)	Typ(1)	Typ(1)	Typ(1)	Typ(1)	
XC7V585T	I_{CCINTQ} + 2700	I_{CCAUXQ} + 40	I_{CCOQ} + 60 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA
XC7V2000T	I_{CCINTQ} + 4000	I_{CCAUXQ} + 80	I_{CCOQ} + 60 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 176	mA
XC7VX330T	I_{CCINTQ} + 1000	I_{CCAUXQ} + 65	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 95	mA
XC7VX415T	I_{CCINTQ} + 1200	I_{CCAUXQ} + 75	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 115	mA
XC7VX485T	I_{CCINTQ} + 1200	I_{CCAUXQ} + 80	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 140	mA
XC7VX550T	I_{CCINTQ} + 3300	I_{CCAUXQ} + 143	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 57 mA per bank	$I_{CCBRAMQ}$ + 200	mA
XC7VX690T	I_{CCINTQ} + 3300	I_{CCAUXQ} + 143	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 57 mA per bank	$I_{CCBRAMQ}$ + 200	mA
XC7VX980T	I_{CCINTQ} + 6500	I_{CCAUXQ} + 202	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 60 mA per bank	$I_{CCBRAMQ}$ + 204	mA
XC7VX1140T	I_{CCINTQ} + 8000	I_{CCAUXQ} + 235	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 63 mA per bank	$I_{CCBRAMQ}$ + 256	mA

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate maximum power-on currents.

Table 8: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
T_{VCCAUX_IO}	Ramp time from GND to 90% of V_{CCAUX_IO}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	$T_J = 100°C$(1)	–	500	ms
		$T_J = 85°C$(1)	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 90% of $V_{MGTVCCAUX}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 9: **SelectIO DC Input and Output Levels(1)(2)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8	–8
HSTL_I_12	–0.300	V_{REF} – 0.080	V_{REF} + 0.080	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	6.3	–6.3
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8	–8
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16	–16
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16	–16
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 3	Note 3
LVCMOS15, LVDCI_15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 4	Note 4
LVCMOS18, LVDCI_18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS25	–0.300	0.700	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 6	Note 6
LVCMOS33	–0.300	0.800	2.000	3.450	0.400	V_{CCO} – 0.400	Note 6	Note 6
LVTTL	–0.300	0.800	2.000	3.450	0.400	2.400	Note 7	Note 7
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.1	–0.1
PCI33_3	–0.400	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.5	–0.5
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	14.25	–14.25
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.0	–13.0
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.9	–8.9
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.0	–13.0
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.9	–8.9
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8	–8
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.4	–13.4

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in 3.3V I/O banks.
3. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks and 4, 8, or 12 mA in HR I/O banks.
4. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, or 16 mA in HR I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, 16, or 24 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, or 16 mA
7. Supported drive strengths of 4, 8, 12, 16, or 24 mA
8. For detailed interface specific DC voltage levels, see the *7 Series FPGAs SelectIO Resources User Guide* (UG471).

LVDS DC Specifications (LVDS_25)

The LVDS standard is available in the HR I/O banks.

Table 12: **LVDS_25 DC Specifications(1)**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply voltage		2.375	2.500	2.625	V
V_{OH}	Output High voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.700	–	–	V
V_{ODIFF}	Differential output voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output common-mode voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential input voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input common-mode voltage		0.300	1.200	1.425	V

Notes:

1. Differential inputs for LVDS_25 can be placed in banks with V_{CCO} levels that are different from the required level for outputs. Consult the *7 Series FPGAs SelectIO Resources User Guide* (UG471) for more information.

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks.

Table 13: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply voltage		1.710	1.800	1.890	V
V_{OH}	Output High voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.825	–	–	V
V_{ODIFF}	Differential output voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output common-mode voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential input voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	Common-mode input voltage = 1.25V	100	350	600	mV
V_{ICM}	Input common-mode voltage	Differential input voltage = ±350 mV	0.300	1.200	1.425	V

Notes:

1. Differential inputs for LVDS can be placed in banks with V_{CCO} levels that are different from the required level for outputs. Consult the *7 Series FPGAs SelectIO Resources User Guide* (UG471) for more information.

IOB Pad Input/Output/3-State

Table 19 (3.3V high-range IOB (HR)) and Table 20 (1.8V high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than T_{IOTP} when the DCITERMDISABLE pin is used. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 19: **3.3V IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
LVTTL_S4	1.31	1.42	1.64	3.77	3.90	4.00	4.53	4.76	4.99	ns
LVTTL_S8	1.31	1.42	1.64	3.50	3.64	3.73	4.26	4.50	4.72	ns
LVTTL_S12	1.31	1.42	1.64	3.49	3.62	3.72	4.25	4.48	4.71	ns
LVTTL_S16	1.31	1.42	1.64	3.03	3.17	3.26	3.79	4.03	4.25	ns
LVTTL_S24	1.31	1.42	1.64	3.25	3.39	3.48	4.01	4.25	4.47	ns
LVTTL_F4	1.31	1.42	1.64	3.22	3.36	3.45	3.98	4.22	4.44	ns
LVTTL_F8	1.31	1.42	1.64	2.71	2.84	2.93	3.47	3.70	3.92	ns
LVTTL_F12	1.31	1.42	1.64	2.69	2.82	2.92	3.45	3.68	3.91	ns
LVTTL_F16	1.31	1.42	1.64	2.57	2.85	3.15	3.33	3.71	4.14	ns
LVTTL_F24	1.31	1.42	1.64	2.41	2.64	2.89	3.17	3.50	3.88	ns
LVDS_25(1)	0.64	0.68	0.80	1.36	1.47	1.55	2.12	2.33	2.54	ns
MINI_LVDS_25	0.68	0.70	0.79	1.36	1.47	1.55	2.12	2.33	2.54	ns
BLVDS_25(1)	0.65	0.69	0.80	1.83	2.02	2.20	2.59	2.88	3.19	ns
RSDS_25 (point to point)(1)	0.63	0.68	0.79	1.36	1.48	1.55	2.12	2.34	2.54	ns
PPDS_25(1)	0.65	0.69	0.80	1.36	1.49	1.58	2.12	2.35	2.57	ns
TMDS_33(1)	0.72	0.76	0.86	1.43	1.54	1.60	2.19	2.40	2.59	ns
PCI33_3(1)	1.28	1.41	1.65	2.71	3.08	3.52	3.47	3.94	4.51	ns
HSUL_12	0.63	0.64	0.71	1.77	1.90	2.00	2.53	2.76	2.99	ns
DIFF_HSUL_12	0.58	0.61	0.70	1.55	1.68	1.78	2.31	2.54	2.77	ns
HSTL_I_S	0.61	0.64	0.73	1.55	1.69	1.80	2.31	2.55	2.79	ns
HSTL_II_S	0.61	0.64	0.73	1.21	1.34	1.43	1.97	2.20	2.42	ns
HSTL_I_18_S	0.64	0.67	0.76	1.28	1.39	1.45	2.04	2.25	2.44	ns
HSTL_II_18_S	0.64	0.67	0.76	1.18	1.31	1.40	1.94	2.17	2.39	ns
DIFF_HSTL_I_S	0.63	0.67	0.77	1.42	1.54	1.61	2.18	2.40	2.60	ns
DIFF_HSTL_II_S	0.63	0.67	0.77	1.15	1.24	1.27	1.91	2.10	2.26	ns
DIFF_HSTL_I_18_S	0.65	0.69	0.78	1.27	1.38	1.43	2.03	2.24	2.42	ns
DIFF_HSTL_II_18_S	0.65	0.69	0.78	1.14	1.23	1.26	1.90	2.09	2.25	ns
HSTL_I_F	0.61	0.64	0.73	1.10	1.19	1.23	1.86	2.05	2.22	ns

Table 19: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
LVCMOS15_F4	0.66	0.69	0.81	1.63	1.76	1.86	2.39	2.62	2.85	ns
LVCMOS15_F8	0.66	0.69	0.81	1.79	1.99	2.18	2.55	2.85	3.17	ns
LVCMOS15_F12	0.66	0.69	0.81	1.40	1.54	1.65	2.16	2.40	2.64	ns
LVCMOS15_F16	0.66	0.69	0.81	1.37	1.51	1.61	2.13	2.37	2.60	ns
LVCMOS12_S4	0.88	0.91	1.00	2.53	2.67	2.76	3.29	3.53	3.75	ns
LVCMOS12_S8	0.88	0.91	1.00	2.05	2.18	2.28	2.81	3.04	3.27	ns
LVCMOS12_S12(1)	0.88	0.91	1.00	1.75	1.89	1.98	2.51	2.75	2.97	ns
LVCMOS12_F4	0.88	0.91	1.00	1.94	2.07	2.17	2.70	2.93	3.16	ns
LVCMOS12_F8	0.88	0.91	1.00	1.50	1.64	1.73	2.26	2.50	2.72	ns
LVCMOS12_F12(1)	0.88	0.91	1.00	1.54	1.71	1.87	2.30	2.57	2.86	ns
SSTL135_S	0.61	0.64	0.73	1.27	1.40	1.50	2.03	2.26	2.49	ns
SSTL15_S	0.61	0.64	0.73	1.24	1.37	1.47	2.00	2.23	2.46	ns
SSTL18_I_S	0.64	0.67	0.76	1.59	1.74	1.85	2.35	2.60	2.84	ns
SSTL18_II_S	0.64	0.67	0.76	1.27	1.40	1.50	2.03	2.26	2.49	ns
DIFF_SSTL135_S	0.59	0.61	0.73	1.27	1.40	1.50	2.03	2.26	2.49	ns
DIFF_SSTL15_S	0.63	0.67	0.77	1.24	1.37	1.47	2.00	2.23	2.46	ns
DIFF_SSTL18_I_S	0.65	0.69	0.78	1.50	1.63	1.72	2.26	2.49	2.71	ns
DIFF_SSTL18_II_S	0.65	0.69	0.78	1.13	1.22	1.25	1.89	2.08	2.24	ns
SSTL135_F	0.61	0.64	0.73	1.04	1.17	1.26	1.80	2.03	2.25	ns
SSTL15_F	0.61	0.64	0.73	1.04	1.17	1.26	1.80	2.03	2.25	ns
SSTL18_I_F	0.64	0.67	0.76	1.12	1.22	1.26	1.88	2.08	2.25	ns
SSTL18_II_F	0.64	0.67	0.76	1.05	1.18	1.28	1.81	2.04	2.27	ns
DIFF_SSTL135_F	0.59	0.61	0.73	1.04	1.17	1.26	1.80	2.03	2.25	ns
DIFF_SSTL15_F	0.63	0.67	0.77	1.04	1.17	1.26	1.80	2.03	2.25	ns
DIFF_SSTL18_I_F	0.65	0.69	0.78	1.10	1.19	1.23	1.86	2.05	2.22	ns
DIFF_SSTL18_II_F	0.65	0.69	0.78	1.02	1.10	1.14	1.78	1.96	2.13	ns

Notes:

1. This I/O standard is only available in the 3.3V high-range (HR) banks.

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
DIFF_HSTL_I_18_F	0.75	0.79	0.92	1.04	1.16	1.24	1.68	1.91	2.06	ns
DIFF_HSTL_II_18_F	0.75	0.79	0.92	0.98	1.09	1.16	1.62	1.85	1.98	ns
DIFF_HSTL_I_DCI_18_F	0.75	0.79	0.92	1.04	1.16	1.24	1.67	1.91	2.06	ns
DIFF_HSTL_II_DCI_18_F	0.75	0.79	0.92	0.98	1.09	1.16	1.61	1.85	1.98	ns
DIFF_HSTL_II _T_DCI_18_F	0.75	0.79	0.92	1.04	1.16	1.24	1.67	1.91	2.06	ns
LVCMOS18_S2	0.47	0.50	0.60	3.95	4.28	4.85	4.59	5.04	5.67	ns
LVCMOS18_S4	0.47	0.50	0.60	2.67	2.98	3.43	3.31	3.73	4.26	ns
LVCMOS18_S6	0.47	0.50	0.60	2.14	2.38	2.72	2.77	3.14	3.54	ns
LVCMOS18_S8	0.47	0.50	0.60	1.98	2.21	2.52	2.61	2.97	3.35	ns
LVCMOS18_S12	0.47	0.50	0.60	1.70	1.91	2.17	2.34	2.67	2.99	ns
LVCMOS18_S16	0.47	0.50	0.60	1.57	1.75	1.97	2.20	2.51	2.79	ns
LVCMOS18_F2	0.47	0.50	0.60	3.50	3.87	4.48	4.14	4.63	5.30	ns
LVCMOS18_F4	0.47	0.50	0.60	2.23	2.50	2.87	2.87	3.25	3.69	ns
LVCMOS18_F6	0.47	0.50	0.60	1.80	2.00	2.26	2.43	2.76	3.08	ns
LVCMOS18_F8	0.47	0.50	0.60	1.46	1.72	2.04	2.10	2.47	2.86	ns
LVCMOS18_F12	0.47	0.50	0.60	1.26	1.40	1.53	1.89	2.16	2.35	ns
LVCMOS18_F16	0.47	0.50	0.60	1.19	1.33	1.44	1.83	2.08	2.26	ns
LVCMOS15_S2	0.59	0.62	0.73	3.55	3.89	4.45	4.19	4.65	5.27	ns
LVCMOS15_S4	0.59	0.62	0.73	2.45	2.70	3.06	3.08	3.45	3.89	ns
LVCMOS15_S6	0.59	0.62	0.73	2.24	2.51	2.88	2.88	3.26	3.71	ns
LVCMOS15_S8	0.59	0.62	0.73	1.91	2.16	2.49	2.55	2.91	3.31	ns
LVCMOS15_S12	0.59	0.62	0.73	1.77	1.98	2.23	2.41	2.73	3.05	ns
LVCMOS15_S16	0.59	0.62	0.73	1.62	1.81	2.02	2.26	2.56	2.84	ns
LVCMOS15_F2	0.59	0.62	0.73	3.38	3.69	4.18	4.02	4.44	5.00	ns
LVCMOS15_F4	0.59	0.62	0.73	2.04	2.21	2.44	2.68	2.97	3.26	ns
LVCMOS15_F6	0.59	0.62	0.73	1.47	1.74	2.09	2.10	2.50	2.91	ns
LVCMOS15_F8	0.59	0.62	0.73	1.31	1.46	1.61	1.95	2.22	2.43	ns
LVCMOS15_F12	0.59	0.62	0.73	1.21	1.34	1.45	1.84	2.10	2.27	ns
LVCMOS15_F16	0.59	0.62	0.73	1.18	1.31	1.41	1.82	2.07	2.23	ns
LVCMOS12_S2	0.64	0.67	0.78	3.38	3.80	4.48	4.02	4.55	5.30	ns
LVCMOS12_S4	0.64	0.67	0.78	2.62	2.94	3.43	3.26	3.70	4.25	ns
LVCMOS12_S6	0.64	0.67	0.78	2.05	2.33	2.72	2.69	3.08	3.54	ns
LVCMOS12_S8	0.64	0.67	0.78	1.94	2.18	2.51	2.58	2.94	3.33	ns
LVCMOS12_F2	0.64	0.67	0.78	2.84	3.15	3.62	3.48	3.90	4.44	ns
LVCMOS12_F4	0.64	0.67	0.78	1.97	2.18	2.44	2.61	2.93	3.26	ns
LVCMOS12_F6	0.64	0.67	0.78	1.33	1.51	1.70	1.96	2.26	2.52	ns
LVCMOS12_F8	0.64	0.67	0.78	1.27	1.42	1.55	1.91	2.18	2.37	ns
LVDCI_18	0.47	0.50	0.60	1.99	2.15	2.35	2.62	2.91	3.17	ns

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
SSTL15_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
SSTL15_DCI_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
SSTL15_T_DCI_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
SSTL135_F	0.69	0.72	0.82	0.88	1.00	1.08	1.52	1.76	1.90	ns
SSTL135_DCI_F	0.69	0.72	0.82	0.89	1.00	1.08	1.52	1.76	1.90	ns
SSTL135_T_DCI_F	0.69	0.72	0.82	0.89	1.00	1.08	1.52	1.76	1.90	ns
SSTL12_F	0.69	0.72	0.82	0.88	1.00	1.08	1.52	1.76	1.90	ns
SSTL12_DCI_F	0.69	0.72	0.82	0.91	1.03	1.11	1.54	1.79	1.93	ns
SSTL12_T_DCI_F	0.69	0.72	0.82	0.91	1.03	1.11	1.54	1.79	1.93	ns
DIFF_SSTL18_I_F	0.75	0.79	0.92	0.94	1.06	1.15	1.58	1.82	1.97	ns
DIFF_SSTL18_II_F	0.75	0.79	0.92	0.97	1.09	1.16	1.61	1.84	1.99	ns
DIFF_SSTL18_I_DCI_F	0.75	0.79	0.92	0.89	1.02	1.10	1.53	1.77	1.92	ns
DIFF_SSTL18_II_DCI_F	0.75	0.79	0.92	0.89	1.02	1.10	1.53	1.77	1.92	ns
DIFF_SSTL18_II_T_DCI_F	0.75	0.79	0.92	0.89	1.02	1.10	1.53	1.77	1.92	ns
DIFF_SSTL15_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
DIFF_SSTL15_DCI_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
DIFF_SSTL15_T_DCI_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
DIFF_SSTL135_F	0.69	0.72	0.82	0.88	1.00	1.08	1.52	1.76	1.90	ns
DIFF_SSTL135_DCI_F	0.69	0.72	0.82	0.89	1.00	1.08	1.52	1.76	1.90	ns
DIFF_SSTL135_T_DCI_F	0.69	0.72	0.82	0.89	1.00	1.08	1.52	1.76	1.90	ns
DIFF_SSTL12_F	0.69	0.72	0.82	0.88	1.00	1.08	1.52	1.76	1.90	ns
DIFF_SSTL12_DCI_F	0.69	0.72	0.82	0.91	1.03	1.11	1.54	1.79	1.93	ns
DIFF_SSTL12_T_DCI_F	0.69	0.72	0.82	0.91	1.03	1.11	1.54	1.79	1.93	ns

Notes:

1. This I/O standard is only available in the 1.8V high-performance (HP) banks.

Table 21 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than T_{IOTPHZ} when the DCITERMDISABLE pin is used. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 21: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
T_{IOTPHZ}	T input to pad high-impedance	0.76	0.86	0.99	ns
$T_{IOIBUFDISABLE\_HR}$	IBUF turn-on time from IBUFDISABLE to O output for HR I/O banks	1.72	1.89	2.14	ns
$T_{IOIBUFDISABLE\_HP}$	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	1.31	1.46	1.76	ns

Input/Output Logic Switching Characteristics

Table 22: **ILOGIC Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
Setup/Hold					
T_{ICE1CK}/T_{ICKCE1}	CE1 pin setup/hold with respect to CLK	0.42/0.00	0.48/0.00	0.67/0.00	ns
T_{ISRCK}/T_{ICKSR}	SR pin setup/hold with respect to CLK	0.53/0.01	0.61/0.01	0.99/0.01	ns
$T_{IDOCKE2}/T_{IOCKDE2}$	D pin setup/hold with respect to CLK without delay (HP I/O banks only)	0.01/0.27	0.01/0.29	0.01/0.34	ns
$T_{IDOCKDE2}/T_{IOCKDDE2}$	DDLY pin setup/hold with respect to CLK (using IDELAY) (HP I/O banks only)	0.01/0.27	0.02/0.29	0.02/0.34	ns
$T_{IDOCKE3}/T_{IOCKDE3}$	D pin setup/hold with respect to CLK without delay (HR I/O banks only)	0.01/0.27	0.01/0.29	0.01/0.34	ns
$T_{IDOCKDE3}/T_{IOCKDDE3}$	DDLY pin setup/hold with respect to CLK (using IDELAY) (HR I/O banks only)	0.01/0.27	0.02/0.29	0.02/0.34	ns
Combinatorial					
T_{IDIE2}	D pin to O pin propagation delay, no delay (HP I/O banks only)	0.09	0.10	0.12	ns
T_{IDIDE2}	DDLY pin to O pin propagation delay (using IDELAY) (HP I/O banks only)	0.10	0.11	0.13	ns
T_{IDIE3}	D pin to O pin propagation delay, no delay (HR I/O banks only)	0.09	0.10	0.12	ns
T_{IDIDE3}	DDLY pin to O pin propagation delay (using IDELAY) (HR I/O banks only)	0.10	0.11	0.13	ns
Sequential Delays					
T_{IDLOE2}	D pin to Q1 pin using flip-flop as a latch without delay (HP I/O banks only)	0.36	0.39	0.45	ns
$T_{IDLODE2}$	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY) (HP I/O banks only)	0.36	0.39	0.45	ns
T_{IDLOE3}	D pin to Q1 pin using flip-flop as a latch without delay (HR I/O banks only)	0.36	0.39	0.45	ns
$T_{IDLODE3}$	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY) (HR I/O banks only)	0.36	0.39	0.45	ns
T_{ICKQ}	CLK to Q outputs	0.47	0.50	0.58	ns
$T_{RQ\_ILOGICE2}$	SR pin to OQ/TQ out (HP I/O banks only)	0.84	0.94	1.16	ns
$T_{GSRQ\_ILOGICE2}$	Global set/reset to Q outputs (HP I/O banks only)	7.60	7.60	10.51	ns
$T_{RQ\_ILOGICE3}$	SR pin to OQ/TQ out (HR I/O banks only)	0.84	0.94	1.16	ns
$T_{GSRQ\_ILOGICE3}$	Global set/reset to Q outputs (HR I/O banks only)	7.60	7.60	10.51	ns
Set/Reset					
$T_{RPW\_ILOGICE2}$	Minimum pulse width, SR inputs (HP I/O banks only)	0.54	0.63	0.63	ns, Min
$T_{RPW\_ILOGICE3}$	Minimum pulse width, SR inputs (HR I/O banks only)	0.54	0.63	0.63	ns, Min

Table 23: **OLOGIC Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
Setup/Hold					
T_{ODCK}/T_{OCKD}	D1/D2 pins setup/hold with respect to CLK	0.45/–0.13	0.50/–0.13	0.58/–0.13	ns
T_{OOCECK}/T_{OCKOCE}	OCE pin setup/hold with respect to CLK	0.28/0.03	0.29/0.03	0.45/0.03	ns
T_{OSRCK}/T_{OCKSR}	SR pin setup/hold with respect to CLK	0.32/0.18	0.38/0.18	0.70/0.18	ns
T_{OTCK}/T_{OCKT}	T1/T2 pins setup/hold with respect to CLK	0.49/–0.16	0.56/–0.16	0.68/–0.16	ns
T_{OTCECK}/T_{OCKTCE}	TCE pin setup/hold with respect to CLK	0.28/0.01	0.30/0.01	0.45/0.01	ns
Combinatorial					
T_{ODQ}	D1 to OQ out or T1 to TQ out	0.73	0.81	0.97	ns
Sequential Delays					
T_{OCKQ}	CLK to OQ/TQ out	0.41	0.43	0.49	ns
$T_{RQ\_OLOGICE2}$	SR pin to OQ/TQ out (HP I/O banks only)	0.63	0.70	0.83	ns
$T_{GSRQ\_OLOGICE2}$	Global set/reset to Q outputs (HP I/O banks only)	7.60	7.60	10.51	ns
$T_{RQ\_OLOGICE3}$	SR pin to OQ/TQ out (HR I/O banks only)	0.63	0.70	0.83	ns
$T_{GSRQ\_OLOGICE3}$	Global set/reset to Q outputs (HR I/O banks only)	7.60	7.60	10.51	ns
Set/Reset					
$T_{RPW\_OLOGICE2}$	Minimum pulse width, SR inputs (HP I/O banks only)	0.54	0.54	0.63	ns, Min
$T_{RPW\_OLOGICE3}$	Minimum pulse width, SR inputs (HR I/O banks only)	0.54	0.54	0.63	ns, Min

Table 32: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
$T_{DSPDO\_A\_P}$	A input to P output not using multiplier	1.30	1.48	1.76	ns
$T_{DSPDO\_C\_P}$	C input to P output	1.13	1.30	1.55	ns
Combinatorial Delays from Input Pins to Cascading Output Pins					
$T_{DSPDO\_\{A; B\}\_\{ACOUT; BCOUT\}}$	{A, B} input to {ACOUT, BCOUT} output	0.47	0.53	0.63	ns
$T_{DSPDO\_\{A, B\}\_CARRYCASCOUT\_MULT}$	{A, B} input to CARRYCASCOUT output using multiplier	3.44	3.94	4.69	ns
$T_{DSPDO\_D\_CARRYCASCOUT\_MULT}$	D input to CARRYCASCOUT output using multiplier	3.36	3.85	4.58	ns
$T_{DSPDO\_\{A, B\}\_CARRYCASCOUT}$	{A, B} input to CARRYCASCOUT output not using multiplier	1.50	1.72	2.04	ns
$T_{DSPDO\_C\_CARRYCASCOUT}$	C input to CARRYCASCOUT output	1.34	1.53	1.83	ns
Combinatorial Delays from Cascading Input Pins to All Output Pins					
$T_{DSPDO\_ACIN\_P\_MULT}$	ACIN input to P output using multiplier	3.09	3.55	4.24	ns
$T_{DSPDO\_ACIN\_P}$	ACIN input to P output not using multiplier	1.16	1.33	1.59	ns
$T_{DSPDO\_ACIN\_ACOUT}$	ACIN input to ACOUT output	0.32	0.37	0.45	ns
$T_{DSPDO\_ACIN\_CARRYCASCOUT\_MULT}$	ACIN input to CARRYCASCOUT output using multiplier	3.30	3.79	4.52	ns
$T_{DSPDO\_ACIN\_CARRYCASCOUT}$	ACIN input to CARRYCASCOUT output not using multiplier	1.37	1.57	1.87	ns
$T_{DSPDO\_PCIN\_P}$	PCIN input to P output	0.94	1.08	1.29	ns
$T_{DSPDO\_PCIN\_CARRYCASCOUT}$	PCIN input to CARRYCASCOUT output	1.15	1.32	1.57	ns
Clock to Outs from Output Register Clock to Output Pins					
$T_{DSPCKO\_P\_PREG}$	CLK PREG to P output	0.33	0.35	0.39	ns
$T_{DSPCKO\_CARRYCASCOUT\_PREG}$	CLK PREG to CARRYCASCOUT output	0.44	0.50	0.59	ns
Clock to Outs from Pipeline Register Clock to Output Pins					
$T_{DSPCKO\_P\_MREG}$	CLK MREG to P output	1.42	1.64	1.96	ns
$T_{DSPCKO\_CARRYCASCOUT\_MREG}$	CLK MREG to CARRYCASCOUT output	1.63	1.87	2.24	ns
$T_{DSPCKO\_P\_ADREG\_MULT}$	CLK ADREG to P output using multiplier	2.30	2.63	3.13	ns
$T_{DSPCKO\_CARRYCASCOUT\_ADREG\_MULT}$	CLK ADREG to CARRYCASCOUT output using multiplier	2.51	2.87	3.41	ns
Clock to Outs from Input Register Clock to Output Pins					
$T_{DSPCKO\_P\_AREG\_MULT}$	CLK AREG to P output using multiplier	3.34	3.83	4.55	ns
$T_{DSPCKO\_P\_BREG}$	CLK BREG to P output not using multiplier	1.39	1.59	1.88	ns
$T_{DSPCKO\_P\_CREG}$	CLK CREG to P output not using multiplier	1.43	1.64	1.95	ns
$T_{DSPCKO\_P\_DREG\_MULT}$	CLK DREG to P output using multiplier	3.32	3.80	4.51	ns

Table 32: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
Clock to Outs from Input Register Clock to Cascading Output Pins					
$T_{DSPCKO\_\{ACOUT;\ BCOUT\}\_\{AREG;\ BREG\}}$	CLK (ACOUT, BCOUT) to {A,B} register output	0.55	0.62	0.74	ns
$T_{DSPCKO\_CARRYCASCOUT\_\{AREG,\ BREG\}\_MULT}$	CLK (AREG, BREG) to CARRYCASCOUT output using multiplier	3.55	4.06	4.84	ns
$T_{DSPCKO\_CARRYCASCOUT\_\ BREG}$	CLK (BREG) to CARRYCASCOUT output not using multiplier	1.60	1.82	2.16	ns
$T_{DSPCKO\_CARRYCASCOUT\_\ DREG\_MULT}$	CLK (DREG) to CARRYCASCOUT output using multiplier	3.52	4.03	4.79	ns
$T_{DSPCKO\_CARRYCASCOUT\_\ CREG}$	CLK (CREG) to CARRYCASCOUT output	1.64	1.88	2.23	ns
Maximum Frequency					
F_{MAX}	With all registers used	741.84	650.20	547.95	MHz
F_{MAX_PATDET}	With pattern detector	627.35	549.75	463.61	MHz
$F_{MAX\_MULT\_NOMREG}$	Two register multiply without MREG	412.20	360.75	303.77	MHz
$F_{MAX\_MULT\_NOMREG\_PATDET}$	Two register multiply without MREG with pattern detect	374.25	327.65	276.01	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG}$	Without ADREG	468.82	408.66	342.70	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG\_PATDET}$	Without ADREG with pattern detect	468.82	408.66	342.58	MHz
$F_{MAX\_NOPIPELINEREG}$	Without pipeline registers (MREG, ADREG)	306.84	267.81	225.02	MHz
$F_{MAX\_NOPIPELINEREG\_PATDET}$	Without pipeline registers (MREG, ADREG) with pattern detect	285.23	249.13	209.38	MHz

Table 38: **MMCM Specification *(Cont'd)***

Symbol	Description	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
MMCM_$T_{LOCKMAX}$	MMCM maximum Lock Time	100	100	100	µs
MMCM_F_{OUTMAX}	MMCM maximum output frequency	1066.00	933.00	800.00	MHz
MMCM_F_{OUTMIN}	MMCM minimum output frequency(5)(6)	4.69	4.69	4.69	MHz
MMCM_$T_{EXTFDVAR}$	External clock feedback variation	< 20% of clock input period or 1 ns Max			
MMCM_$RST_{MINPULSE}$	Minimum reset pulse width	5.00	5.00	5.00	ns
MMCM_F_{PFDMAX}	Maximum frequency at the phase frequency detector	550.00	500.00	450.00	MHz
MMCM_F_{PFDMIN}	Minimum frequency at the phase frequency detector	10.00	10.00	10.00	MHz
MMCM_$T_{FBDELAY}$	Maximum delay in the feedback path	3 ns Max or one CLKIN cycle			
MMCM Switching Characteristics Setup and Hold					
$T_{MMCMDCK\_PSEN}$/ $T_{MMCMCKD\_PSEN}$	Setup and hold of phase-shift enable	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMDCK\_PSINCDEC}$/ $T_{MMCMCKD\_PSINCDEC}$	Setup and hold of phase-shift increment/decrement	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMCKO\_PSDONE}$	Phase shift clock-to-out of PSDONE	0.59	0.68	0.81	ns
Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK					
$T_{MMCMDCK\_DADDR}$/ $T_{MMCMCKD\_DADDR}$	DADDR setup/hold	1.25/0.15	1.40/0.15	1.63/0.15	ns, Min
$T_{MMCMDCK\_DI}$/$T_{MMCMCKD\_DI}$	DI setup/hold	1.25/0.15	1.40/0.15	1.63/0.15	ns, Min
$T_{MMCMDCK\_DEN}$/$T_{MMCMCKD\_DEN}$	DEN setup/hold	1.76/0.00	1.97/0.00	2.29/0.00	ns, Min
$T_{MMCMDCK\_DWE}$/$T_{MMCMCKD\_DWE}$	DWE setup/hold	1.25/0.15	1.40/0.15	1.63/0.15	ns, Min
$T_{MMCMCKO\_DRDY}$	CLK to out of DRDY	0.65	0.72	0.99	ns, Max
F_{DCK}	DCLK frequency	200.00	200.00	200.00	MHz, Max

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard. See http://www.xilinx.com/products/intellectual-property/clocking_wizard.htm.
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.
6. When CLKOUT4_CASCADE = TRUE, MMCM_F_{OUTMIN} is 0.036 MHz.

Additional Package Parameter Guidelines

The parameters in this section provide the necessary values for calculating timing budgets for Virtex-7 T and XT FPGA clock transmitter and receiver data-valid windows.

Table 50: **Package Skew**

Symbol	Description	Device	Package	Value	Units
$T_{PKGSKEW}$	Package Skew(1)	XC7V585T	FFG1157	232	ps
			FFG1761	255	ps
		XC7V2000T	FHG1761	308	ps
			FLG1925	266	ps
		XC7VX330T	FFG1157	170	ps
			FFG1761	270	ps
		XC7VX415T	FFG1157	203	ps
			FFG1158	237	ps
			FFG1927	183	ps
		XC7VX485T	FFG1157	191	ps
			FFG1158	209	ps
			FFG1761	274	ps
			FFG1927	209	ps
			FFG1930	304	ps
		XC7VX550T	FFG1158	217	ps
			FFG1927	254	ps
		XC7VX690T	FFG1157	239	ps
			FFG1158	217	ps
			FFG1761	284	ps
			FFG1926	238	ps
			FFG1927	254	ps
			FFG1930	287	ps
		XC7VX980T	FFG1926	242	ps
			FFG1928	199	ps
			FFG1930	243	ps
		XC7VX1140T	FLG1926	271	ps
			FLG1928	216	ps
			FLG1930	279	ps

Notes:

1. These values represent the worst-case skew between any two SelectIO resources in the package: shortest delay to longest delay from die pad to ball.
2. Package delay information is available for these device/package combinations. This information can be used to deskew the package.

GTX Transceiver Specifications

GTX Transceiver DC Input and Output Levels

Table 51 summarizes the DC specifications of the GTX transceivers in Virtex-7 T and XT FPGAs. Consult the *7 Series FPGAs GTX/GTH Transceiver User Guide* (UG476) for further details.

Table 51: **GTX Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPOUT}	Differential peak-to-peak output voltage(1)	Transmitter output swing is set to maximum setting	–	–	1000	mV
$V_{CMOUTDC}$	DC common mode output voltage.	Equation based	$V_{MGTAVTT} - DV_{PPOUT}/4$			mV
R_{OUT}	Differential output resistance		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew		–	2	12	ps
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled)	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Absolute input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–200	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
R_{IN}	Differential input resistance		–	100	–	Ω
C_{EXT}	Recommended external AC coupling capacitor(2)		–	100	–	nF

Notes:

1. The output swing and preemphasis levels are programmable using the attributes discussed in the *7 Series FPGAs GTX/GTH Transceiver User Guide* (UG476), and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

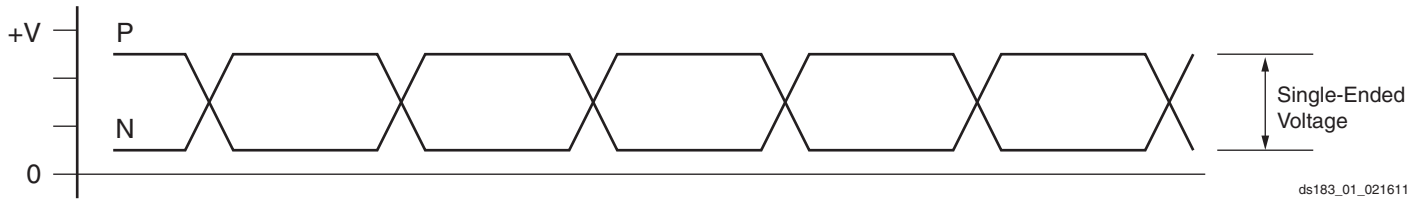

Figure 1: **Single-Ended Peak-to-Peak Voltage**

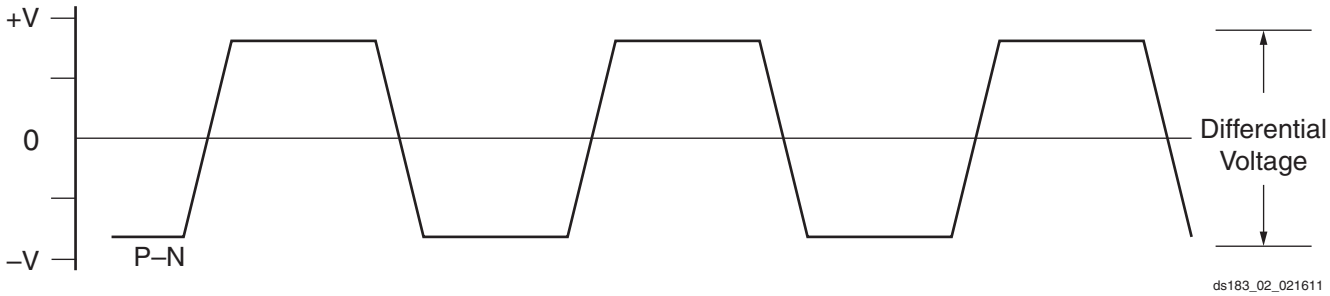

Figure 2: **Differential Peak-to-Peak Voltage**

GTX Transceiver Protocol Jitter Characteristics

For Table 60 through Table 65, the *7 Series FPGAs GTX/GTH Transceiver User Guide* (UG476) contains recommended settings for optimal usage of protocol specific characteristics.

Table 60: **Gigabit Ethernet Protocol Characteristics (GTX Transceivers)**

Description	Line Rate (Mb/s)	Min	Max	Units
Gigabit Ethernet Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	1250	–	0.24	UI
Gigabit Ethernet Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	1250	0.749	–	UI

Table 61: **XAUI Protocol Characteristics (GTX Transceivers)**

Description	Line Rate (Mb/s)	Min	Max	Units
XAUI Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	3125	–	0.35	UI
XAUI Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	3125	0.65	–	UI

Table 62: **PCI Express Protocol Characteristics (GTX Transceivers)(1)**

Standard	Description		Line Rate (Mb/s)	Min	Max	Units
PCI Express Transmitter Jitter Generation						
PCI Express Gen 1	Total transmitter jitter		2500	–	0.25	UI
PCI Express Gen 2	Total transmitter jitter		5000	–	0.25	UI
PCI Express Gen 3(2)	Total transmitter jitter uncorrelated		8000	–	31.25	ps
	Deterministic transmitter jitter uncorrelated			–	12	ps
PCI Express Receiver High Frequency Jitter Tolerance						
PCI Express Gen 1	Total receiver jitter tolerance		2500	0.65	–	UI
PCI Express Gen 2(3)	Receiver inherent timing error		5000	0.40	–	UI
	Receiver inherent deterministic timing error			0.30	–	UI
PCI Express Gen 3(2)	Receiver sinusoidal jitter tolerance	0.03 MHz–1.0 MHz	8000	1.00	–	UI
		1.0 MHz–10 MHz		Note 4	–	UI
		10 MHz–100 MHz		0.10	–	UI

Notes:

1. Tested per card electromechanical (CEM) methodology.
2. PCI-SIG 3.0 certification and compliance test boards are currently not available.
3. Using common REFCLK.
4. Between 1 MHz and 10 MHz the minimum sinusoidal jitter roll-off with a slope of 20dB/decade.

GTH Transceiver Specifications

GTH Transceiver DC Input and Output Levels

Table 66 summarizes the DC specifications of the GTH transceivers in Virtex-7 T and XT FPGAs. Consult the *7 Series FPGAs GTX/GTH Transceiver User Guide* (UG476) for further details.

Table 66: **GTH Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled)	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Absolute input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–400	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
DV_{PPOUT}	Differential peak-to-peak output voltage(1)	Transmitter output swing is set to 1010	–	–	800	mV
$V_{CMOUTDC}$	Common mode output voltage: DC coupled	Equation based	$V_{MGTAVTT} - DV_{PPOUT}/4$			mV
$V_{CMOUTAC}$	Common mode output voltage: AC coupled	Equation based	$V_{MGTAVTT} - DV_{PPOUT}/2$			mV
R_{IN}	Differential input resistance		–	100	–	Ω
R_{OUT}	Differential output resistance		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew		–	–	10	ps
C_{EXT}	Recommended external AC coupling capacitor(2)		–	100	–	nF

Notes:

1. The output swing and preemphasis levels are programmable using the attributes discussed in the *7 Series FPGAs GTX/GTH Transceiver User Guide* (UG476), and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

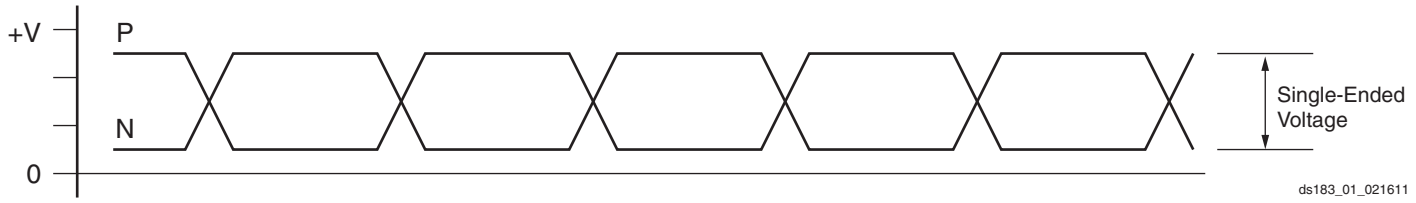

Figure 4: **Single-Ended Peak-to-Peak Voltage**

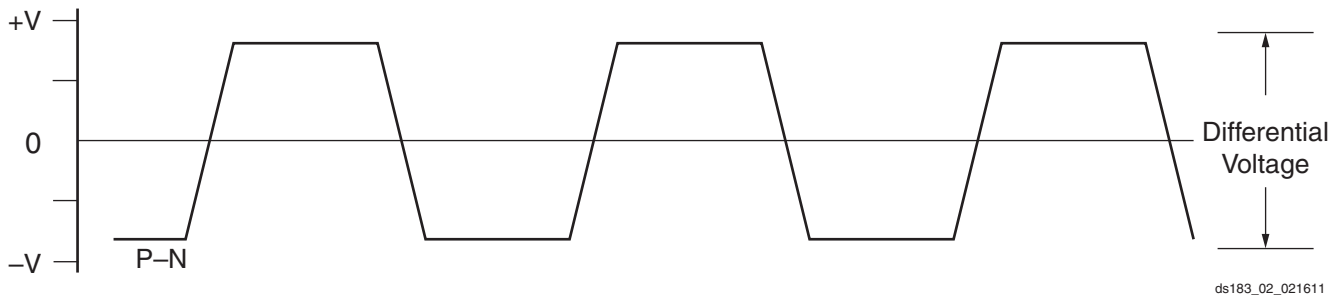

Figure 5: **Differential Peak-to-Peak Voltage**

Table 70: **GTH Transceiver Reference Clock Switching Characteristics**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range		60	–	820	MHz
T_{RCLK}	Reference clock rise time	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle	Transceiver PLL only	40	50	60	%

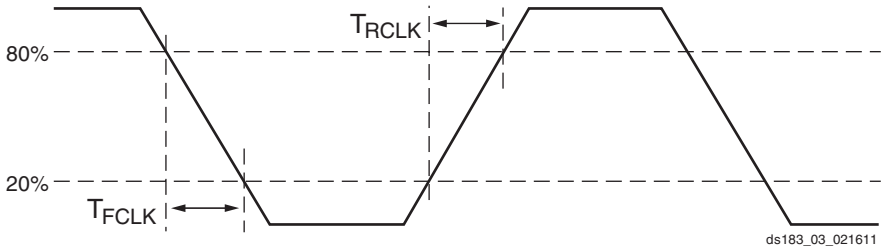

Figure 6: **Reference Clock Timing Parameters**

Table 71: **GTH Transceiver PLL/Lock Time Adaptation**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T_{LOCK}	Initial PLL lock		–	–	1	ms
T_{DLOCK}	Clock recovery phase acquisition and adaptation time for decision feedback equalizer (DFE).	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	–	50,000	37×10^6	UI
	Clock recovery phase acquisition and adaptation time for low-power mode (LPM) when the DFE is disabled.		–	50,000	2.3×10^6	UI

Table 83: **Configuration Switching Characteristics *(Cont'd)***

Symbol	Description	Virtex-7 T and XT Devices	Speed Grade			Units
			-3	-2/-2L/-2G	-1	
Master/Slave Serial Mode Programming Switching						
T_{DCCK}/T_{CCKD}	DIN setup/hold		4.0/0.0	4.0/0.0	4.0/0.0	ns, Min
T_{CCO}	DOUT clock to out		8.0	8.0	8.0	ns, Max
SelectMAP Mode Programming Switching						
T_{SMDCCK}/T_{SMCCKD}	D[31:00] setup/hold		4.0/0.0	4.0/0.0	4.0/0.0	ns, Min
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B setup/hold		4.0/0.0	4.0/0.0	4.0/0.0	ns, Min
T_{SMWCCK}/T_{SMCCKW}	RDWR_B setup/hold		10.0/0.0	10.0/0.0	10.0/0.0	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 Ω pull-up resistor required)		7.0	7.0	7.0	ns, Max
T_{SMCO}	D[31:00] clock to out in readback		8.0	8.0	8.0	ns, Max
F_{RBCCK}	Readback frequency	SLR-based	70	70	70	MHz, Max
		All other devices	100	100	100	MHz, Max
Boundary-Scan Port Timing Specifications						
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI setup/hold	SLR-based	9.0/2.0	9.0/2.0	9.0/2.0	ns, Min
		All other devices	3.0/2.0	3.0/2.0	3.0/2.0	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output	SLR-based	17	17	17	ns, Max
		All other devices	7.0	7.0	7.0	ns, Max
F_{TCK}	TCK frequency	SLR-based	20	20	20	MHz, Max
		All other devices	66	66	66	MHz, Max
BPI Master Flash Mode Programming Switching						
T_{BPICCO} (2)	A[28:00], RS[1:0], FCS_B, FOE_B, FWE_B, ADV_B clock to out		8.5	8.5	8.5	ns, Max
T_{BPIDCC}/T_{BPICCD}	D[15:00] setup/hold		4.0/0.0	4.0/0.0	4.0/0.0	ns, Min
SPI Master Flash Mode Programming Switching						
T_{SPIDCC}/T_{SPICCD}	D[03:00] setup/hold		3.0/0.0	3.0/0.0	3.0/0.0	ns, Min
T_{SPICCM}	MOSI clock to out		8.0	8.0	8.0	ns, Max
$T_{SPICCFC}$	FCS_B clock to out		8.0	8.0	8.0	ns, Max

Notes:

1. To support longer delays in configuration, use the design solutions described in the *7 Series FPGA Configuration User Guide* (UG470).
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.

eFUSE Programming Conditions

Table 84 lists the programming conditions specifically for eFUSE. For more information, see the *7 Series FPGA Configuration User Guide* (UG470).

Table 84: **eFUSE Programming Conditions** (1)

Symbol	Description	Min	Typ	Max	Units
I_{FS}	V_{CCAUX} supply current	–	–	115	mA
t_j	Temperature range	15	–	125	°C

Notes:

1. The FPGA must not be configured during eFUSE programming.

Date	Version	Description
03/27/2013	1.13	In Table 7, added values for the XC7VX330T and XC7VX415T devices. Revised Table 15 and Table 16 to include production release of the XC7VX330T and XC7VX415T. In Table 18, updated the table title, LPDDR2 values, and removed Note 3. Removed Note 2: *For QPLL line rate, the maximum line rate with the divider N set to 66 is 10.3125 Gb/s* from Table 68.
04/17/2013	1.14	Updated the AC Switching Characteristics section with production release changes to Table 15 and Table 16 for XC7VX550T for all speed specifications. In Table 1, revised V_{IN} (I/O input voltage) to match values in Table 4 and Table 5, and combined Note 4 with old Note 5 and then added new Note 5. Revised V_{IN} description and added Note 8 in Table 2. Updated first 3 rows in Table 4 and Table 5. Updated values and added new values to Table 7. Also revised PCI33_3 voltage minimum in Table 10 to match values in Table 1, Table 4, and Table 5. Added Note 1 to Table 12 and Table 13. Throughout the data sheet (Table 29, Table 30, and Table 45) removed the obvious note “A Zero “0” Hold Time listing indicates no hold time or a negative hold time.” Updated and clarified USRCLK data in Table 57 and Table 72.

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